

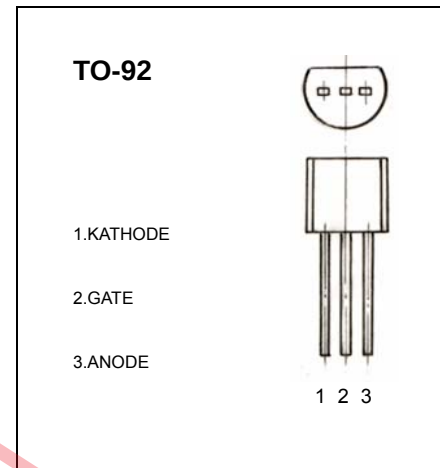


TO-92 Plastic-Encapsulate Transistors

MCR 100- 6,- 8 Silicon Planar PNP Thyristor

MAIN FEATURES

Symbol		value	unit
$I_{T(RMS)}$		0.8	A
V_{DRM}/V_{RRM}	MCR100-6	400	V
	MCR100-8	600	
T_J	Junction Temperature	-40 to 125	°C
T_{stg}	Storage Temperature	-55 to 150	°C



DESCRIPTION

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

FEATURES

- Blocking voltage to 400 V (MCR100-6)
- RMS on-state current to 0.8 A
- General purpose switching

APPLICATIONS

- General purpose switching
- Phase control applications
- Solid state relays.

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
On state voltage *	V_{TM}	$I_{TM}=1A$		1.7	V
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V
Peak Repetitive forward and reverse blocking voltage MCR100-6 MCR100-8	V_{DRM} AND V_{RRM}	$I_{DRM}=10\mu A$	400 600		V
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}	$V_{AK}=\text{Rated}$ V_{DRM} or V_{RRM}		10	μA
Holding current	I_H	$I_{HL}=20mA, V_{AK}=7V$		5	mA
Gate trigger current	I_{GT}	A2	5	15	μA
		A1	15	30	μA
		A	30	80	μA
		B	80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq$ 1%.

Typical Characteristics

MCR100-6,-8

FIGURE 1 – MCR100-8 CURRENT DERATING
(REFERENCE: CASE TEMPERATURE)

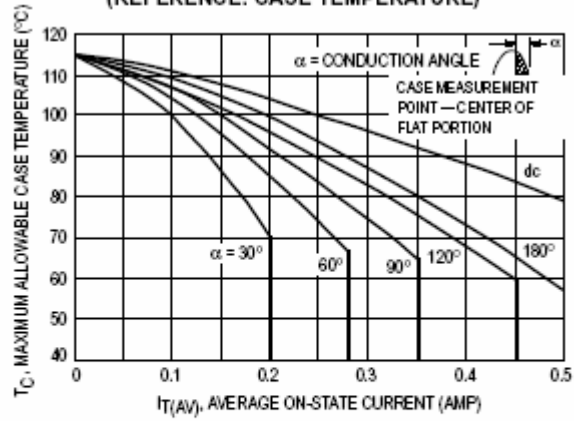


FIGURE 2 – MCR100-8 CURRENT DERATING
(REFERENCE: AMBIENT TEMPERATURE)

